

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S5	1	("6153520").PN.	USPAT; USOCR	OR	OFF	2004/10/25 10:43
S9	1	("6524939").PN.	USPAT; USOCR	OR	OFF	2005/09/22 14:22
S12	7	(("6291839") or ("6078064") or ("5804839") or ("6008539") or ("6335218") or ("6258618") or ("5438006")).PN.	USPAT; USOCR	OR	OFF	2007/02/16 09:40
S13	1	5656832.PN.	USPAT	OR	ON	2004/10/21 14:56
S15	0	(438/671.ccls. with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:08
S16	0	("438"/\$.ccls. with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:08
S17	0	("257"/\$.ccls. with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:07
S18	197	(438/671).COLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/18 07:07
S19	0	((438/671.ccls.) with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:08
S20	8999	(semiconductor with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:38
S21	24	(semiconductor with (dry adj etch\$5) with (light adj emitting adj device)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:40

S22	15	(semiconductor with (dry adj etch\$5) with (light adj emitting adj device)) and metal and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:49
S23	3	(semiconductor with metal with (dry adj etch\$5) with (light adj emitting adj device)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:10
S24	134	((semiconductor) with ((silicon or ("S")) adj (layer or film))) and ((metal adj (film or layer)) with (dry adj etch\$5))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:40
S25	1	("6777294").PN.	USPAT; USOCR	OR	OFF	2007/08/05 09:31
S26	1	("6790718").PN.	USPAT; USOCR	OR	OFF	2007/02/07 16:09
S27	1	("20040185599").PN.	US-PGPUB	OR	OFF	2006/03/27 14:40
S28	3764	(semiconductor with (dry adj etch\$5)) and metal and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:49
S29	173	(semiconductor near (dry adj etch\$5)) and metal and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:49
S30	60	(semiconductor near (dry adj etch\$5)) and (metal adj (layer or film)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:48
S31	0	(semiconductor adj body) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) near (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:50
S32	6	(semiconductor adj body) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:51

S33	15	(semiconductor adj body) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:56
S34	373	(interconnect\$4) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:56
S35	365	semiconductor and (interconnect\$4) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 15:20
S36	15	semiconductor and (interconnect\$3) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927" and (platinum and palladium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 15:22
S37	137	semiconductor and (interconnect\$3) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) and (dry adj etch\$5)) and @ad<="20010927" and (platinum and palladium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 15:22
S38	16	substrate and ((nitride adj compound adj semiconductor) adj (layer or film)) and (metal adj (layer or film)) and (dry adj etch\$4) and partial\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/30 13:29
S39	1	("5836029").PN.	USPAT; USOCR	OR	OFF	2007/02/08 14:42
S42	3	("6562465").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/08 14:42

S43	12	((("5838029") or ("5814533") or ("7096873") or ("7071015") or ("6969873") or ("6858866") or ("6735230") or ("6680492") or ("6657237") or ("6376866") or ("6087681") or ("6083841")).pn.)	USPAT; USOCR	OR	OFF	2007/02/13 10:54
S44	2	((("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841").pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) with ((silicon adj oxide) or ("SiO. sub.2"))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 11:16
S45	9	((("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841").pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO. sub.2"))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 11:15
S46	0	((("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841").pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) near ((silicon adj oxide) or ("SiO. sub.2"))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 11:15
S47	8	((("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841").pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) same ((silicon adj oxide) or ("SiO. sub.2"))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:14

S48	0	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841").pn. and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) same ((silicon adj oxide) or ("SiO. sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:14
S49	0	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841").pn. and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO. sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:14
S50	0	(nitride adj compound adj semiconductor) and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:15
S51	1	(nitride adj compound adj semiconductor) and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:15
S52	1	("5838029").PN.	USPAT; USOCR	OR	OFF	2007/08/05 18:40
S53	1	("7096873").PN.	USPAT; USOCR	OR	OFF	2007/08/05 19:01
S55	12	(("7096873") or ("7071015") or ("6969873") or ("6858866") or ("6735230") or ("6680492") or ("6657237") or ("6376866") or ("6087681") or ("6083841") or ("5656832") or ("5838029")).PN.	USPAT; USOCR	OR	OFF	2007/08/05 20:17
S56	154	(compound adj semiconductor) and (metal with (dry adj etch\$5)) and @ad<= "20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/01 22:57

S57	10	(compound adj semiconductor) and (metal near (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/01 22:57
S58	9	(nitride adj compound adj semiconductor) and (metal with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/01 22:59
S62	152	(nitrid\$4 adj compound adj semiconductor) and (metal and ((dry adj etch\$5) or ("RI'E") or ("RI'BE")))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 13:11
S63	12	(nitrid\$4 adj compound adj semiconductor) and (metal with ((dry adj etch\$5) or ("RI'E") or ("RI'BE")))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:01
S64	25	(nitrid\$4 adj compound adj semiconductor) and (metal same ((dry adj etch\$5) or ("RI'E") or ("RI'BE")))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:02
S65	9	(nitrid\$4 adj compound adj semiconductor) and (metal with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:02
S66	1	("7,096,873").PN.	USPAT	OR	OFF	2008/06/03 15:03
S67	1	(nitrid\$4 adj compound adj semiconductor) and (metal and ((dry adj etch\$5) or ("RI'E") or ("RI'BE")))) and @ad<="20010927" and (sputter\$ adj back)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 20:27
S69	1	10/813530	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 10:18
S70	53	((light adj emit\$4 adj (device or structure)) or ("LED")) and ((metal adj (layer or film)) with (dry adj etch\$4)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 10:20

S71	1	((light adj emit\$4 adj (device or structure)) or ("LED")) and ((metal adj (layer or film)) with (dry adj etch\$4)) and (nitride adj compound) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 15:04
S72	9	(nitride adj compound) and ((metal adj (layer or film)) with (dry adj etch\$4)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 15:05
S73	350805	((light adj emit\$4 adj (device or structure)) or ("LED")) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 15:07
S74	705	S73 and (nitride adj compound)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 15:07
S75	1	S74 and ((metal adj (layer or film)) with (dry adj etch\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 15:08
S76	2495	(438/706).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15:09
S77	738	(438/712).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15:09
S78	147	(438/273).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15:12
S79	412	(438/210).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15:12

S80	557	(438/250).COLS	US-PGPUB; USPAT; USOCR; FFPS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15.12
S81	899	(438/660).COLS	US-PGPUB; USPAT; USOCR; FFPS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15.13
S82	226	(438/670).COLS.	US-PGPUB; USPAT; USOCR; FFPS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15:13
S83	1060	(438/669).COLS.	US-PGPUB; USPAT; USOCR; FFPS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/25 15:14
S84	1330	((reactive adj ion adj etch \$3) or ("RIE")) near (dry adj etch\$) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 22:36
S85	218	((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 22:36
S86	173	((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$) and @ad<="20010927" and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/25 22:36
S87	2	(("6083841") or ("20020173062")).PN.	US-PGPUB; USPAT	OR	OFF	2008/11/26 09:58
S88	47	((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) with ((silicon adj oxide) or ("SiO sub.2")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:49

S89	108	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) with ((silicon adj oxide) or ("SiO.sub.2")) or ((silicon adj nitride) or ("SiN")))	US-PGPUB; USPAT; USOCP; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:50
S90	16	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) with ((silicon adj oxide) or ("SiO.sub.2")) and ((silicon adj nitride) or ("SiN")))	US-PGPUB; USPAT; USOCP; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:50
S91	2	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) near ((silicon adj oxide) or ("SiO.sub.2")) and ((silicon adj nitride) or ("SiN")))	US-PGPUB; USPAT; USOCP; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:55
S92	0	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) adj ((silicon adj oxide) or ("SiO.sub.2")) and ((silicon adj nitride) or ("SiN")))	US-PGPUB; USPAT; USOCP; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:55
S93	89	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) near ((silicon adj oxide) or ("SiO.sub.2")) or ((silicon adj nitride) or ("SiN")))	US-PGPUB; USPAT; USOCP; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:55

S94	85	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) adj ((silicon adj oxide) or ("SiO.sub.2")) or ((silicon adj nitride) or ("SiN")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:55
S95	14	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) near ((silicon adj oxide) or ("SiO.sub.2"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:56
S96	8	(((reactive adj ion adj etch \$3) or ("RIE")) adj (dry adj etch\$)) and @ad<="20010927" and semiconductor and ((mask\$ or photo or photoresist or resist) adj ((silicon adj oxide) or ("SiO.sub.2"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 08:56
S97	3	(("5277750") or ("20020173062") or ("6083841")).PN.	US-PGPUB; USPAT	OR	OFF	2008/12/07 21:45
S98	4	((("5277750") or ("20020173062") or ("6083841") or ("6448162")) .PN.	US-PGPUB; USPAT	OR	OFF	2008/12/17 08:28
S99	1	(("7038252").PN.	US-PGPUB; USPAT	OR	OFF	2008/12/17 13:18
S101	1	11/681408	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 13:31
S102	5	((("5277750") or ("20020173062") or ("6083841") or ("6448162") or ("6,379,985")).PN.	US-PGPUB; USPAT	OR	OFF	2008/12/17 19:38
S103	6	((("5277750") or ("20020173062") or ("6083841") or ("6448162") or ("6,379,985") or ("7,096,873")).PN.	US-PGPUB; USPAT	OR	OFF	2008/12/17 21:35
S105	3	((("7268419") or ("7141874") or ("20030025587")).PN.	US-PGPUB; USPAT	OR	OFF	2009/04/29 15:11

S106	1	11/413749	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/29 15:14
S107	1	11/564460	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/30 07:49
S108	1	438/197,204,206.ccls. and (lower adj (gate or electrode)) and (upper adj (gate or electrode)) and (air adj gap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/30 09:28
S109	71	"438"/\$.ccls. and (lower adj (gate or electrode)) and (upper adj (gate or electrode)) and (air adj gap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/30 09:29
S110	135	"257"/\$.ccls. and (lower adj (gate or electrode)) and (upper adj (gate or electrode)) and (air adj gap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/30 09:29
S111	2	("6941537").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/30 09:35
S118	2	(("5277750") or ("6083841")).PN.	US-PGPUB; USPAT	OR	OFF	2009/04/30 11:22
S135	7	(("7307348") or ("20010004129") or ("7268422") or ("6897555") or ("6747356") or ("6489679") or ("6479758")). PN	US-PGPUB; USPAT	OR	OFF	2009/04/30 14:44
S141	0	(nitride adj compound) and ((metal adj (layer or film)) with (dry adj etch\$4)) and @ad<="20010927" and (magnesium or ("Mg")) and (zinc or ("Zn"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:27

S142	997863	(nitride adj compound) and ((metal adj (layer or film)) with (dry adj etch\$4)) and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:28
S143	0	(nitride adj compound) and ((metal adj (layer or film)) with (dry adj etch\$4)) and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:28
S144	0	((semiconductor) with ((silicon or ("S")) adj (layer or film)) and ((metal adj (film or layer)) with (dry adj etch\$5))) and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:29
S145	2174	(implant\$3 or dop\$3) and ("P-type") and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:38
S146	1589	(implant\$3 or dop\$3) with ("P-type") and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:38
S147	1050	(implant\$3 or dop\$3) near ("P-type") and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:39
S148	666	(implant\$3 or dop\$3) adj ("P-type") and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:39
S149	666	((implant\$3 or dop\$3) adj ("P-type")) and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:39
S150	635	((dop\$3) adj ("P-type")) and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:39
S151	540	((doped) adj ("P-type")) and @ad<="20010927" and ((magnesium or ("Mg")) and (zinc or ("Zn"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:39

S152	97	(((doped) adj ("P-type")) with ((magnesium or ("Mg")) and (zinc or ("Zn")))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:40
S153	2	(((doped) adj ("P-type")) adj (((magnesium or ("Mg")) and (zinc or ("Zn")))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:40
S154	30	(((doped) adj ("P-type")) near ((magnesium or ("Mg")) and (zinc or ("Zn")))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:40
S155	12	(((doped) adj ("P-type")) and (((magnesium or ("Mg")) and (zinc or ("Zn")))) and @ad<="20010927" and (ridge adj waveguide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/01 07:47
S156	233	uan and thai and chip and support	USPAT	OR	ON	2009/05/02 09:13

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